WHAT IS CLAIMED IS:

1. A method of fabricating a semiconductor chip from a semiconductor wafer having a first surface supporting a semiconductor element and a second surface opposite the first surface, the method comprising the steps of:

performing isotropic etching at least partially on a cutting portion of the semiconductor wafer from one or both of the first surface and the second surface;

performing anisotropic etching on a remaining portion of the cutting portion from the one or both of the first surface and the second surface, thereby cutting the cutting portion of the semiconductor wafer.

2. The method as claimed in claim 1, further comprising the step of:

forming a resist on the first surface to expose the cutting portion on the first surface, when the cutting portion is isotropically etched from the first surface.

3. The method as claimed in claim 2, wherein the resist has rounded-off corners.

4. The method as claimed in claim 1, further comprising the step of:

forming a resist on the second surface to expose the cutting portion on the second surface, when the cutting portion is isotropically etched from the second surface.

5. The method as claimed in claim 4, wherein the resist has rounded-off corners.

6. A semiconductor chip fabricated from a semiconductor wafer, comprising:

a first surface supporting a semiconductor element; and

a second surface opposite the first surface,

wherein at least one of the first surface and the second surface has rounded-off edges.

7. The semiconductor chip as claimed in claim 6, further comprising notched side surfaces.

8. A semiconductor chip fabricated from a

semiconductor wafer, comprising:

a plurality of rounded-off corners.